METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, AND BONDING APPARATUS

ABSTRACT OF THE DISCLOSURE

In a first bonding step of bonding an initial ball 11a to a pad surface 2, the initial ball 11a is applied by ultrasonic vibration while in pressure contact with the pad surface 2 and a capillary 12 undergoes a scrubbing motion to be rotated spirally. This allows the deformation area of the initial ball 11a to be reduced, whereby the accuracy of bonding can be improved. In a second bonding step of bonding a bonding wire 11 to a lead surface 4, the capillary 12 and the bonding wire 11 are applied by ultrasonic vibration while in pressure contact with the lead surface 4 and the capillary 12 undergoes a scrubbing motion to be rotated spirally. This allows the bonding wire 11 bonded to the lead surface 4 to be cut reliably.

Figure 1